

**256Kx32 Static RAM
CMOS, High Speed
Module**

ADVANCE INFORMATION

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Features

The EDI8M32256C is a high speed 8 megabit Static RAM module organized as 256K words by 32 bits. This module is constructed from eight 256Kx4 Static RAMs in LCC packages on a multi-layered ceramic substrate.

Four chip selects ($\overline{E1-E4}$) are used to independently enable the four bytes. Reading or writing can be executed on individual bytes or any combination of multiple bytes through proper use of selects.

The EDI8M32256C is offered in a 60 pin DIP package which enables 8 megabits of memory to be placed in less than 1.8 square inches of board space.

All inputs and outputs are TTL compatible and operate from a single 5V supply. Fully asynchronous circuitry is used, requiring no clocks or refreshing for operation and providing equal access and cycle times for ease of use.

Military product, incorporating semiconductor components which are compliant to MIL-STD-883, paragraph 1.2.1, is available.

256Kx32 bit CMOS Static Random Access Memory

- Access Times 35, 45, and 55ns
- Individual Byte Selects
- Fully Static, No Clocks
- TTL Compatible I/O

High Density Package

- 60 Pin DIP, No. 86
- Common Data Inputs and Outputs

Single +5V ($\pm 10\%$) Supply Operation

Pin Names

A0-A17	Address Inputs
E1-E4	Chip Enable
W0-W1	Write Enable
DQ0-DQ31	Common Data Input/Output
VCC	Power (+5V $\pm 10\%$)
VSS	Ground

**Pin Configuration
and Block Diagram**

